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DIODES, SILICON, POWER RECTIFIER,

FAST RECOVERY,

BASED ON TYPES 1N5415 THROUGH 1N5420

ESCC Detail Specification No. 5103/007

ISSUE 1 October 2002



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FAST RECOVERY,

BASED ON TYPES 1N5415 THROUGH 1N5420

ESA/SCC Detail Specification No. 5103/007

space components coordination group

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DOCUMENTATION CHANGE NOTICE

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APPENDICES (Applicable to specific Manufacturers only) None.



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1. <u>GENERAL</u>

1.1 <u>SCO</u>PE

This specification details the ratings, physical and electrical characteristics, test and inspection data for Diodes, Silicon, Power Rectifier, Fast Recovery, based on Types 1N5415 through 1N5420.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic diodes specified herein, which are also covered by this specification, are listed in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the diodes specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

1.7 HIGH TEMPERATURE TEST PRECAUTIONS

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in a 100% inert atmosphere.



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TABLE 1(a) - COMPONENT TYPE VARIANTS

| (1) | (2) | (3) | (4) | (5) | (6) | (7) |
|---------|--------|--------------------|----------------------|-------------------------|-----------------------------|-----------------------------|
| VARIANT | TYPE | REVERSE VOLTAGE | BREAKDOWN VOLTAGE | JUNCTION CAPACITANCE | REVERSE RECOVERY TIME | Lead Material and Finish |
| | | (V) | (V) | (pF) | (ns) | |
| 01 | 1N5415 | 50 | 55 | 550 | 150 | A10 |
| 02 | 1N5415 | 50 | 55 | 550 | 150 | A3 or A4 |
| 03 | 1N5416 | 100 | 110 | 430 | 150 | A10 |
| 04 | 1N5416 | 100 | 110 | 430 | 150 | A3 or A4 |
| 05 | 1N5417 | 200 | 220 | 250 | 150 | A10 |
| 06 | 1N5417 | 200 | 220 | 250 | 150 | A3 or A4 |
| 07 | 1N5418 | 400 | 440 | 165 | 150 | A10 |
| 08 | 1N5418 | 400 | 440 | 165 | 150 | A3 or A4 |
| 09 | 1N5419 | 500 | 550 | 140 | 250 | A10 |
| 10 | 1N5419 | 500 | 550 | 140 | 250 | A3 or A4 |
| 11 | 1N5420 | 600 | 660 | 120 | 400 | A10 |
| 12 | 1N5420 | 600 | 660 | 120 | 400 | A3 or A4 |

TABLE 1(b) - MAXIMUM RATINGS

| No. | CHARACTERISTIC | SYMBOL | MAXIMUM RATING | UNIT | NOTES |
|-----|-------------------------------------|------------------|----------------|------|------------------|
| 1 | Forward Surge Current | I _{FSM} | 80 | А | 1 |
| 2 | Reverse Voltage | V _R | See Note 2 | V | |
| 3 | Average Output Rectified Current | lo | 3.0 | А | 3 |
| 4 | Operating Temperature Range | T _{op} | 65 to +175 | °C | T _{amb} |
| 5 | Storage Temperature Range | T _{stg} | - 65 to + 200 | °C | |
| 6 | Soldering Temperature | T _{sol} | + 245 | °C | 4 |

NOTES

- 1. Sinusoidal, with period = 8.3ms maximum.2. See Column 3 of Table 1(a).3. At T_{amb} = \leq + 55°C. For derating of I_O with T_L, see Figure 1.
- 4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the can and the same lead shall not be resoldered until 3 minutes have elapsed.



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FIGURE 1 - PARAMETER DERATING INFORMATION



Temperature(°C)

NOTES

1. L = Lead length from body in inches.

Output Current Derating with Lead Temperature for Different Lead Lengths



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FIGURE 2 - PHYSICAL DIMENSIONS



| SYMBOL | INC | HES | MILLIMETRES | | |
|--------|-------|-------|-------------|------|--|
| STMBOL | MIN. | MAX. | MIN. | MAX. | |
| А | - | 0.145 | - | 3.7 | |
| В | 0.039 | 0.041 | 0.99 | 1.04 | |
| С | - | 0.110 | - | 2.8 | |
| D | - | 0.180 | - | 4.6 | |
| Е | - | 0.300 | - | 7.6 | |
| F | 0.975 | - | 24.8 | - | |
| G | - | 0.120 | - | 3.0 | |
| Н | 2.300 | - | 58.4 | - | |

FIGURE 3 - FUNCTIONAL DIAGRAM

1. Cathode

2. Anode





1. The cathode end shall be marked with a coloured ring.



2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the diodes specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 **DEVIATIONS FROM GENERIC SPECIFICATION**

4.2.1 Deviations from Special In-process Controls None.

4.2.2 Deviations from Final Production Tests (Chart II)

- (a) Bond Strength Test: Shall not be performed.
- (b) Die-shear Test: Shall not be performed.
- (c) Para. 9.7, Particle Impact Noise Detection (PIND) Test: Not applicable.
- (d) The following test shall be added after Para. 9.8.2, Seal Test, Fine and Gross Leak (Optional) and before Para. 9.9.3, Electrical Measurements at Room Temperature:-

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Surge current in accordance with Test method 4066 of MIL-STD-750. The following test conditions shall apply:-

 $\begin{array}{lll} T_{amb} & : & \pm 25 \pm 3 \ ^\circ C. \\ I_{FSM} & : & 80A. \\ Number of pulses & : & 5. \\ Pulse rate & : & 1 \ pulse/minute. \\ t_p & : & 8.3ms. \\ Pulse form & : & sinusoidal. \end{array}$

ste

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) High Temperature Reverse Bias: Shall not be performed.
- (b) Para. 9.12, Radiographic Inspection: Not applicable.

4.2.4 Deviations from Qualification Tests (Chart IV)

- (a) Bond Strength Test: Shall not be performed.
- (b) Die-shear Test: Shall not be performed.
- 4.2.5 Deviations from Lot Acceptance Tests (Chart V) None.
- 4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the diodes specified herein shall be 0.25 grammes.

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition :'A'.Applied Force :22.2 Newtons.Duration :15 seconds.



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MATERIALS AND FINISHES 4.4

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

Glass, hermetically sealed.

4.4.2 Lead Material and Finish

The lead material shall be Type 'A' with either Type '3 or 4' or Type '10' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

| Detail Specification Number | <u>510300702</u> B |
|---------------------------------------|--------------------|
| Type Variant | |
| Testing Level (B or C, as applicable) | |



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL CHARACTERISTICS

4.6.1 <u>Electrical Measurements at Room Temperature</u>

The parameters to be measured at room temperature are scheduled in Table 2. The measurements shall be performed at T_{amb} = +22 ± 3 °C.

4.6.2 <u>Electrical Measurements at High and Low Temperatures</u>

The parameters to be measured at high and low temperatures are scheduled in Table 3.

4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown, where applicable, in MIL-STD-750 and Figure 4.



4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for burn-in shall be as specified in Table 5 of this specification.

4.7.3 <u>Electrical Circuits for Burn-in (Figure 5)</u>

Not applicable.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

| No. | CHARACTERISTICS | SYMBOL | TEST METHOD | DD TEST CONDITION | LIM | UNIT | |
|------|-------------------|-------------------|-------------|-------------------------------------|------|------|------|
| INO. | | OTMDOL | MIL-STD-750 | | MIN. | MAX. | UNIT |
| 1 | Reverse Current | I _R | 4016 | V _R = (1) V | - | 1.0 | μA |
| 2 | Forward Voltage | V _F | 4011 | l _F = 9.0A See Note 2 | 0.6 | 1.5 | V |
| 3 | Breakdown Voltage | V _(BR) | 4021 | l _R = 50μA | (3) | - | V |

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

| No. | CHARACTERISTICS | HARACTERISTICS SYMBOL | TEST METHOD | TEST CONDITION | LIMITS | | UNIT |
|------|--------------------------|-----------------------|-------------|---|--------|------|------|
| 140. | UNA DOTENIO 100 | OTWDOL | MIL-STD-750 | (Note 6) | MIN. | MAX. | UNIT |
| 4 | Junction Capacitance | CJ | 4001 | V _R = 4.0V f = 1.0MHz | - | (4) | pF |
| 5 | Reverse Recovery Time | t _{rr} | 4031 | I _F = 0.5A I _R = 1.0A I _{RR} = 0.25A (See Figure 4) | - | (5) | ns |

NOTES

- 1. See Column 3 of Table 1(a).
- 2. Pulse Measurement with tp = 300μ s; Duty Cycle $\leq 2\%$.
- 3. See Column 4 of Table 1(a).
- 4. See Column 5 of Table 1(a).
- 5. See Column 6 of Table 1(a).
- 6. A.C. parameters shall be performed on a sample basis LTPD = 7, or less (see Annex 1 of ESA/SCC Generic Specification No. 5000).



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TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

| No. | CHARACTERISTICS | SYMBOL | TEST METHOD MIL-STD-750 | TEST CONDITIONS | LIMI MIN. | ITS | UNIT |
|-----|-----------------|----------------|----------------------------|--|--------------|------|------|
| | | | | TEST CONDITIONS | | MAX. | |
| 1 | Reverse Current | l _R | 4016 | V _R = (1) T _{amb} = + 100 (+0-5) °C | - | 20 | μΑ |

<u>NOTES</u>

1. See Column 3 of Table 1(a).

TABLE 4 - PARAMETER DRIFT VALUES

| No. | CHARACTERISTICS | SYMBOL | SPEC. AND/OR TEST METHOD | TEST CONDITION | CHANGE LIMITS (Δ) | UNIT |
|-----|-----------------|----------------|-----------------------------|-------------------|-------------------------|---------|
| 1 | Reverse Current | l _R | As per Table 2 | As per Table 2 | ±0.25 or (1) ±100 | µА % |
| 2 | Forward Voltage | V _F | As per Table 2 | As per Table 2 | ± 100 | mV |

NOTES

1. Whichever is the greater referred to the initial value.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

REVERSE RECOVERY TIME



NOTES

- 1. Oscilloscope: $t_r \le 3.0$ ns; $Z_{IN} = 50\Omega$.2. Pulse Generator: $t_r \le 8.0$ ns; $Z_S = 10\Omega$.
- 3. Current viewing resistor, non-inductive, coaxial.



TABLE 5 - CONDITIONS FOR BURN-IN AND OPERATING LIFE TESTS

| No. | CHARACTERISTICS | SYMBOL | CONDITION | UNIT |
|-----|-------------------------------------|------------------|-----------------------|------|
| 1 | Ambient Temperature | T _{amb} | + 25 ± 3 | °C |
| 2 | Peak Reverse Voltage | V _{RM} | V _{RM} = (1) | Vrms |
| 5 | Frequency | f | 50 to 60 | Hz |
| 4 | Average Output Rectified Current | lo | 3.0 See Note 2 | A |

NOTES

1. See Column 3 of Table 1(a).

2. Mounting shall be performed without bending or soldering the leads. Lead length from body to mounting shall be 0.12 inches (3.14mm) minimum.



4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> SPECIFICATION No. 5000)

4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at T_{amb} = +22±3 °C.

4.8.2 <u>Electrical Measurements at Intermediate Points during Endurance Tests</u>

The parameters to be measured at intermediate points during endurance tests are scheduled in Table 6.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are scheduled in Table 6. The measurements shall be performed at Tamb = $+22 \pm 3$ °C.

4.8.4 <u>Conditions for Operating Life Tests (Part of Endurance Testing)</u>

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 <u>Electrical Circuits for Operating Life Tests (Figure 5)</u> Not applicable.

4.8.6 <u>Conditions for High Temperature Storage Test (Part of Endurance Testing)</u>

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The conditions for high temperature storage shall be T_{amb} = +200 (+0-5) °C.



TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

| No. | CHARACTERISTICS | SYMBOL | SPEC. AND/OR TEST METHOD | TEST CONDITION | LIMITS | | UNIT |
|-----|--------------------------|-----------------|-----------------------------|-------------------|--------|------|------|
| | | | | | MIN. | MAX. | |
| 1 | Reverse Current | l _R | As per Table 2 | As per Table 2 | - | 1.0 | μA |
| 2 | Forward Voltage | V _F | As per Table 2 | As per Table 2 | 0.6 | 1.5 | V |
| 3 | Reverse Recovery Time | t _{rr} | As per Table 2 | As per Table 2 | - | (1) | ns |

NOTES

1. See Column 6 of Table 1(a).